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(54) **Title:** MANAGING WARMUP OPERATIONS IN A MEMORY DEVICE

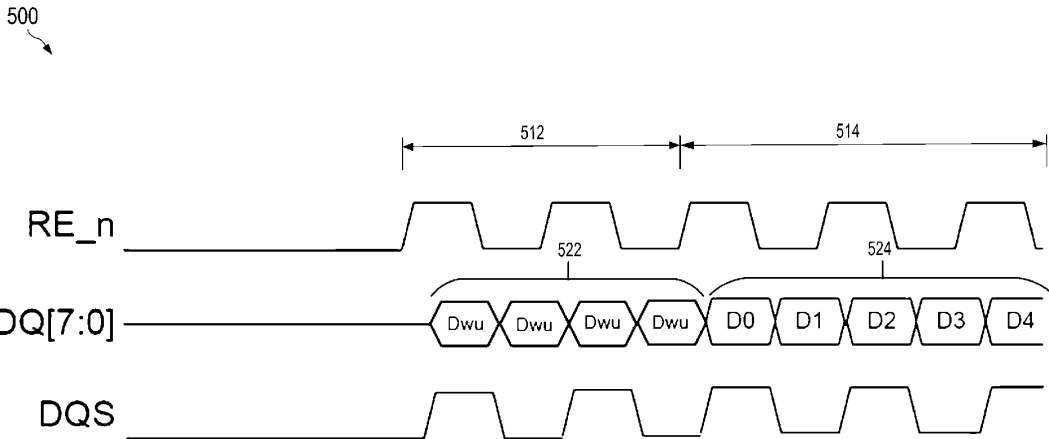


FIG. 5

(57) **Abstract:** Methods, devices, and systems for managing warmup operations in memory devices are provided. In one aspect, an input/output (I/O) interface of a memory device can be configured to receive a first address of first data to be read, receive warmup information that indicates a warmup period before reading the first data, and determine, based on the first address and the warmup information, a second address of second data to be read during the warmup period before reading the first data.